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From models to mechanisms: defects and charge trapping in amorphous silicon nitride

Hückmann, L.

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From Models to Mechanisms: Defects and Charge Trapping in Amorphous Silicon Nitride

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Promotor

Dr. J. Meyer

Co-promotor

Dr. J. P. Cottom

Promotiecommissie

Prof. dr. M. Ubbink

Prof. dr. I. M. N. Groot

Prof. dr. M. I. J. Probert (University of York)

Dr. B. Weber (ARCNL & Universiteit van Amsterdam)

Dr. J. J. Geuchies

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Contents

List of Abbreviations	ix
1 Introduction	1
1.1 Overview of Amorphous Silicon Nitride and its Technological Applications .	1
1.2 Electronic Structure and Defect-Mediated Charge Trapping	3
1.3 Composition and Chemistry in Si–N–O Systems	7
1.4 The Aim of this Thesis	10
References	11
2 Theory and Methods	19
2.1 Description of Solids	20
2.2 Classical Interatomic Potentials	24
2.3 Density Functional Theory	31
2.4 The Gaussian Plane Wave Method	37
2.5 Modeling Solids and Defects	42
References	48
3 Configurations out of Chaos: A Hierarchical Sampling Approach to Amorphous Solids	53
3.1 Amorphous Solids	54
3.2 Generating Atomistic Models of Amorphous Solids	63
3.3 Structural Ensembles Obtained from Advanced Statistical Sampling	68
3.4 Site-Specific Sampling	76
3.5 Summary	81
References	82
4 Application-Tailored Classical Interaction Potentials: A Workflow Based on Bayesian Optimization	89
4.1 Introduction	90
4.2 Methods	94

4.3	Results and Discussion	104
4.4	Discussion	112
4.5	Conclusion	116
4.A	Appendix	118
	References	122
5	Intrinsic Charge Trapping and Reversible Charge Induced Structural Modifications in α - Si_3N_4	127
5.1	Introduction	128
5.2	Results and Discussion	131
5.3	Conclusion and Summary	143
5.4	Computational Details	144
	References	146
6	From Jekyll to Hyde and Beyond: Hydrogen's Multifaceted Role in Passivation, H-Induced Breakdown, and Charging of Amorphous Silicon Nitride	151
6.1	Introduction	153
6.2	Results and Discussion	155
6.3	Conclusion and Summary	166
6.4	Computational Details	166
	References	167
7	Mechanistic Insights into the Dry Oxidation of Amorphous Silicon Nitride	171
7.1	Introduction	173
7.2	Results and Discussion	176
7.3	Discussion	192
7.4	Conclusions	194
7.5	Computational Details	195
	References	197
8	Forged by Charge: Polaron-Induced Matrix Formation in Silicon Nitride Conversion-Type Anodes for Lithium-ion Batteries	203
8.1	Introduction	205
8.2	Results and Discussion	208
8.3	Discussion and Summary	219
8.4	Conclusions	222
8.5	Computational Details	222

References	225
Summary	xi
Nederlandse samenvatting	xvii
Publications	xxiii
Afterword	xxv
Curriculum vitae	xxvii

List of Abbreviations

Mathematical Symbols

x	scalar
\mathbf{x}	vectors
\mathcal{N}	normal distribution

Abbreviations

BO	Bayesian optimization
CBM	conduction band minimum
CTL	charge transition level
DOS	density of states
DFT	density functional theory
EPR	electron paramagnetic resonance
GGA	generalized gradient approximation
GPR	Gaussian process regression
GPW	Gaussian plane waves
HEG	homogeneous electron gas
IPR	inverse participation ratio
KS	Kohn-Sham
LDA	local density approximation
MAE	mean absolute error
MD	molecular dynamics
MQ	melt-quench
PBC	periodic boundary conditions

LIST OF ABBREVIATIONS

RDF		radial distribution function
VACF		velocity autocorrelation function
VBM		valence band maximum
VDOS		vibrational density of states

Physical Quantities

B	GPa	bulk modulus
E_{bg}	eV	band gap
E_{coh}	eV atom ⁻¹	cohesive energy
E_{F}	eV	Fermi energy
E_{form}	eV	formation energy
ϵ_{r}		dielectric constant
$\Delta_{\text{f}}H$	kJ mol ⁻¹	heat of formation
μ	eV	chemical potential
μ_{s}	e	spin moment
ν	Hz	frequency
ρ	g cm ⁻³	mass density
ρ	$e a_0^{-3}$	electron density
q_{mul}	e	Mulliken charge

Kröger-Vink Defect Symbols

X_{S}^q	element X at site S in charge state q
H_{i}	hydrogen interstitials
N_{i}	nitrogen interstitials
V_{N}	nitrogen vacancy
O_{i}	oxygen interstitials
O_{N}	oxygen substitutions on nitrogen sites